Seat No.:	Enrolment No
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## **GUJARAT TECHNOLOGICAL UNIVERSITY**

BE - SEMESTER-III • EXAMINATION – SUMMER • 2014

Subject Code: 131101 Subject Name: Basic Electronics			
Tir	•	02.30 pm - 05.00 pm Total Marks: 70	
	1. 2.	<ul><li>Attempt all questions.</li><li>Make suitable assumptions wherever necessary.</li><li>Figures to the right indicate full marks.</li></ul>	
Q.1	(a) (b)	Explain Hall effect phenomenon and list out its applications. Quantitatively discuss the use of Hall effect to determine mobility.  Derive continuity equation for carrier concentration in body of a semiconductor.	07 07
Q.2	(a)	Discuss the process of splitting of energy levels of isolated atoms into energy bands as these atoms are brought into close proximity to form a crystal.	07
	<b>(b)</b>	Draw diode I-V characteristic, discuss its temperature dependence and obtain expression for diode dynamic resistance.  OR	07
	<b>(b)</b>	Explain working of Tunnel diode. Draw its I-V characteristic and symbol. List out applications of Tunnel diode.	07
Q.3	(a)	For a sinusoidal input of 10 V peak, sketch $I_R$ and $V_O$ in the circuit shown in Fig. Q. 3 (a). Assume ideal diode with cut-in voltage equal to 0.7 V.	07
	<b>(b)</b>	Draw BJT circuit in common-base configuration as well as its input and output characteristics. Explain base-width modulation for the same.  OR	07
Q.3	(a)	A symmetrical 5 KHz square wav that varies between + 10 V and -10 V is impressed upon the clipping circuit shown in Fig. Q: 3(a) OR. Assume for diode: $R_f$ (forward bias resistance) = 0, $R_r$ (reverse bias resistance) = 2 M $\Omega$ , Cut-in voltage = 0. Sketch the steady state output waveform, indicating value of maximum, minimum, and constant portion.	07
	<b>(b)</b>	In diode connected transistor circuit shown in Fig. Q: 3 (b) OR, the transistor has $\beta = 19$ . If $V_E = 4$ V, determine the value of $R_B$ . Neglect base-to-emitter junction voltage in the calculations.	07
Q.4	(a)	Derive expression for $A_I$ , $A_V$ , $Z_i$ , and $Y_O$ for a basic amplifier circuit in terms of h-parameters.	07
	<b>(b)</b>	What do you understand bias compensation? Draw and explain diode compensation circuit for $V_{BE}$ .	07
Q.4	(a)	Derive expression for A <sub>I</sub> , A <sub>V</sub> , Z <sub>i</sub> , and Y <sub>O</sub> for a common-collector amplifier circuit using simplified hybrid model.	07
	<b>(b)</b>	Explain thermal runaway. Show graphically that thermal runaway cannot take place if the quiescent point is located at $V_{CE} < (1/2) \ V_{CC}$ .	07
Q.5	(a) (b)	Draw two-dimensional structure of n-channel MOSFET. Explain its working. Explain push-pull arrangement of transistors and discuss its advantages.  OR	07 07
Q.5	(a) (b)	Explain the use of FET as a voltage variable resistor.  Draw transformer-coupled audio amplifier circuit. Show that the maximum value of conversion efficiency for this circuit is 50 %.	07 07

